Description

JMT P-channel Enhancement Mode Power MOSFET

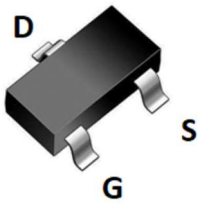
Features

- V_{DS}= -12V, I_D= -8A
  $R_{DS(ON)}$ <18mΩ @ V_{GS} = -4.5V
  $R_{DS(ON)}$ <25mΩ @ V_{GS} = -2.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

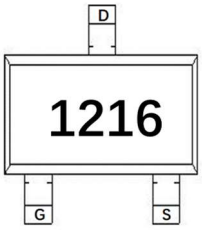
Application

- PWM Applications
- Load Switch
- Power Management

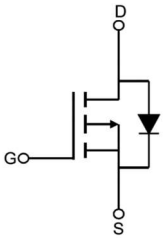
RoHS



SOT-23-3L top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
1216	JMTJ1216A	TAPING	SOT-23-3L	7inch	3000	180000

Absolute Maximum Ratings (T_A=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-12	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Continuous Drain Current	T_A = 25℃	-8	A
		T_A = 100℃	-5.2	A
I_{DM}	Pulsed Drain Current note1		-32	A
P_D	Power Dissipation	T_A = 25℃	1.6	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		78	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-12	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -12V, V_{GS} = 0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D= -250μA	-0.4	-0.7	-1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS} =-4.5V, I_D =-8A	-	14.7	18	mΩ
		V_{GS} =-2.5V, I_D =-5A	-	18	25	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = -6V, V_{GS} = 0V, f = 1.0MHz	-	2700	-	pF
C_{oss}	Output Capacitance		-	680	-	pF
C_{rss}	Reverse Transfer Capacitance		-	590	-	pF
Q_g	Total Gate Charge	V_{DS}= -6V, I_D = -8A, V_{GS} = -4.5V	-	35	-	nC
Q_{gs}	Gate-Source Charge		-	5	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	10	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = -6V, I_D = -4A, V_{GS}=-4.5V, R_{GEN}=2.5Ω	-	11	-	ns
t_r	Turn-on Rise Time		-	35	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	30	-	ns
t_f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-8	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-32	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = -8A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Figure1: Output Characteristics

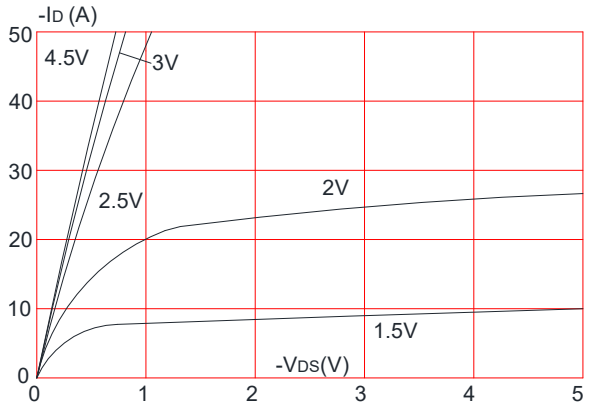


Figure 2: Typical Transfer Characteristics

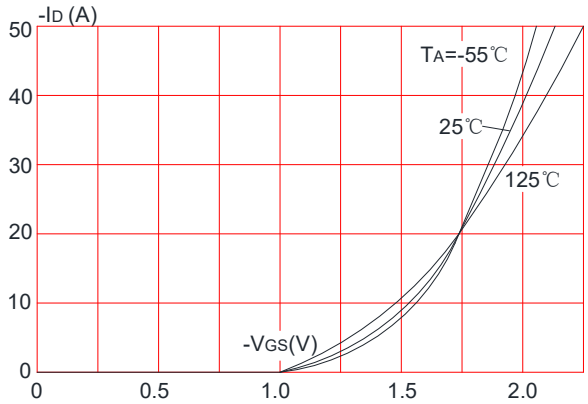


Figure 3: On-resistance vs. Drain Current

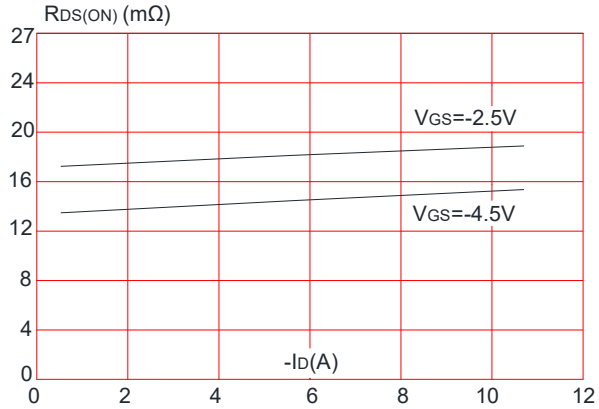


Figure 4: Body Diode Characteristics

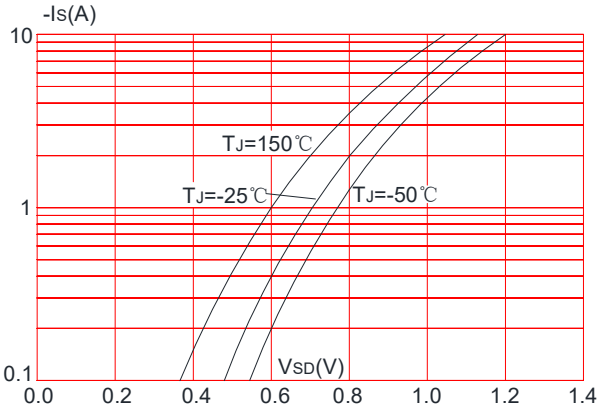


Figure 5: Gate Charge Characteristics

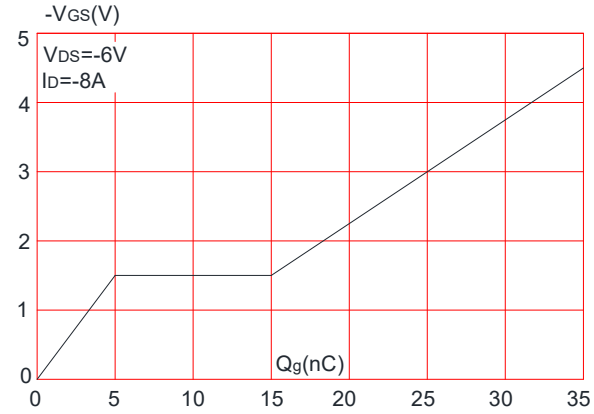


Figure 6: Capacitance Characteristics

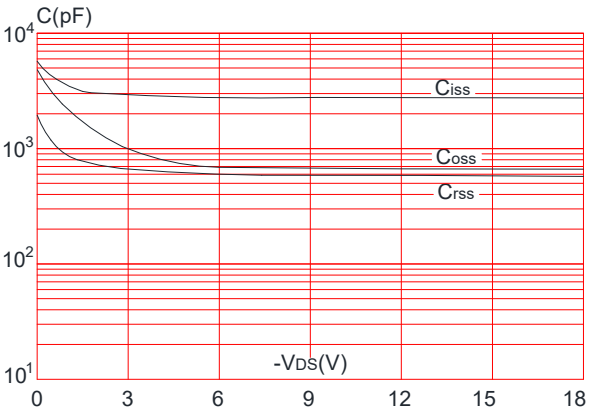


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

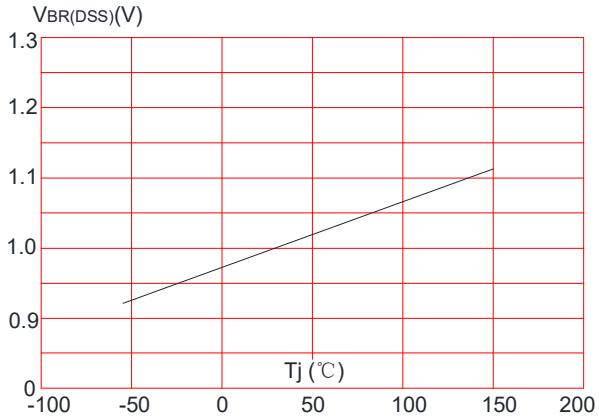


Figure 8: Normalized on Resistance vs. Junction Temperature

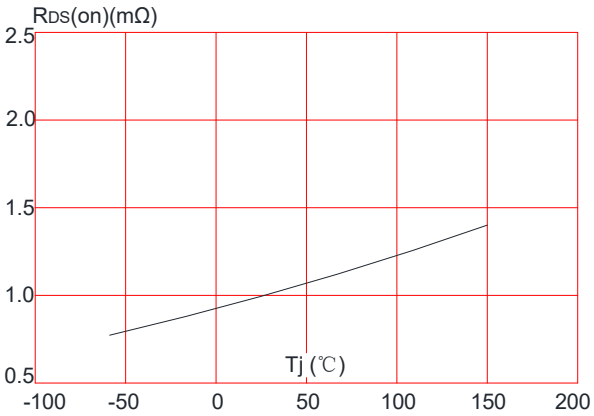


Figure 9: Maximum Safe Operating Area

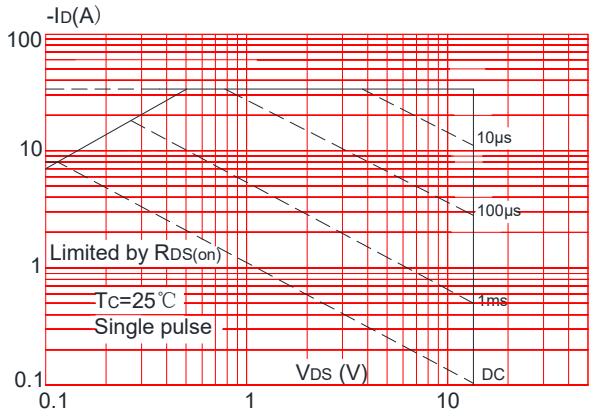


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

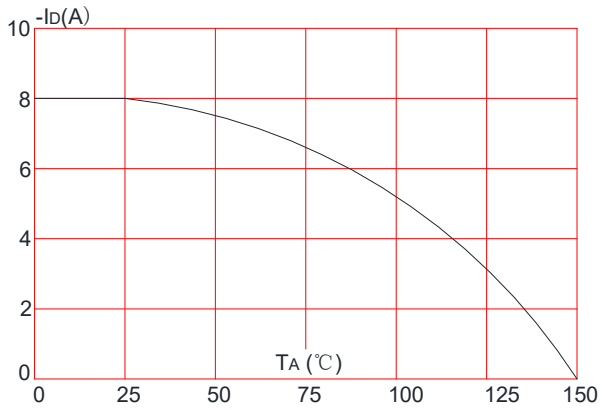
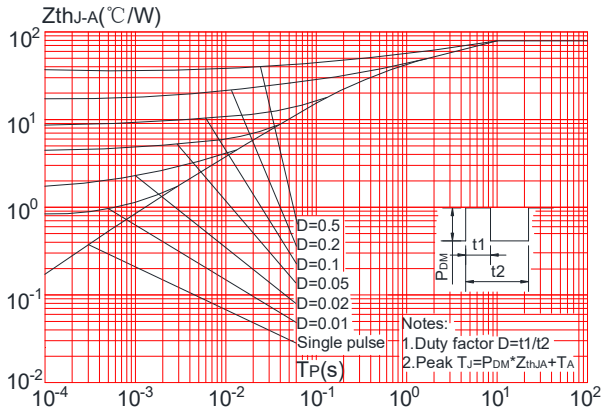
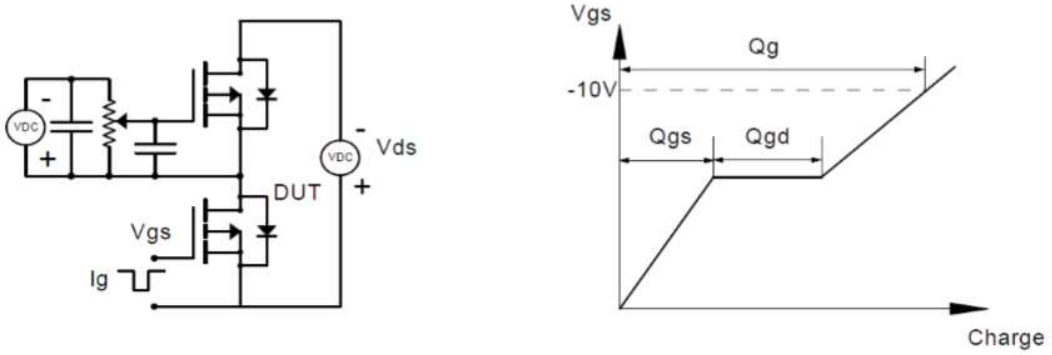


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

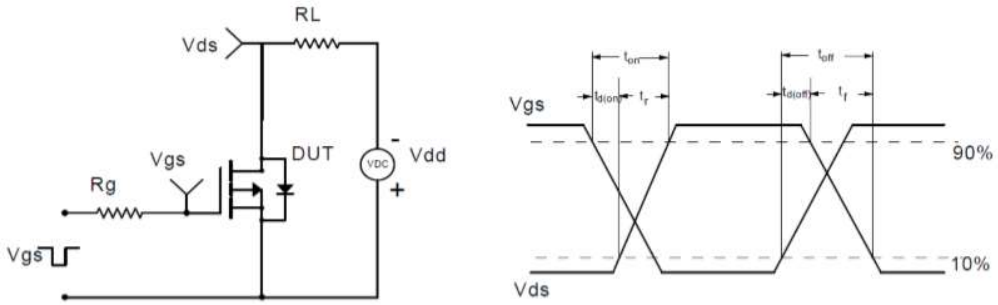


Typical Performance Characteristics

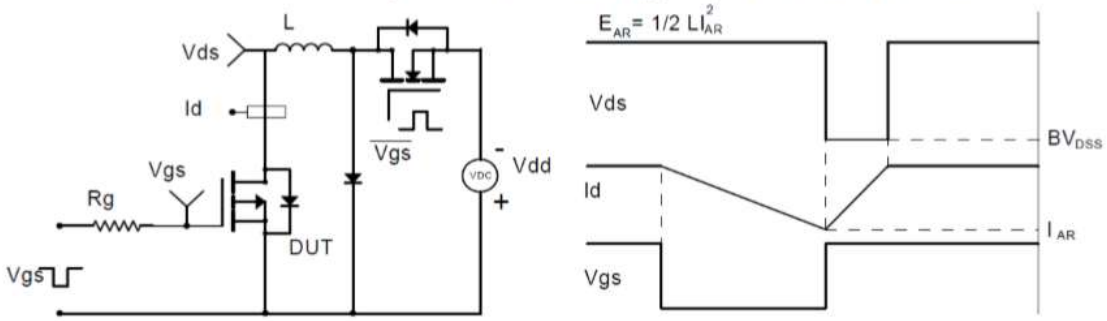
Gate Charge Test Circuit & Waveform



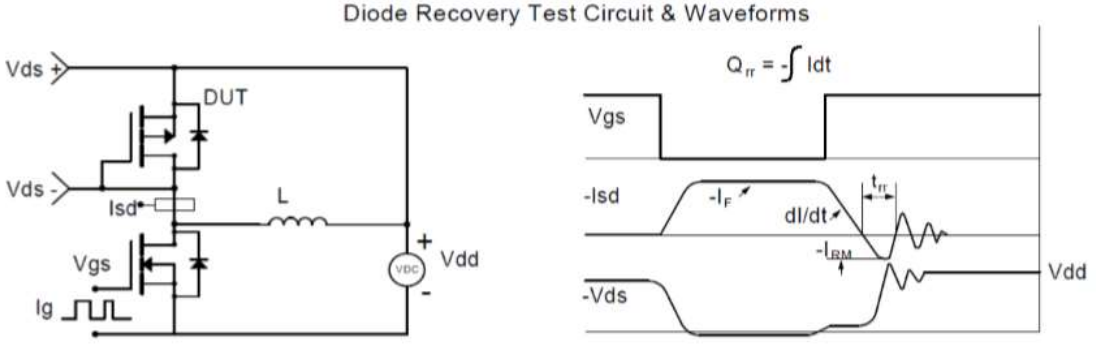
Resistive Switching Test Circuit & Waveforms



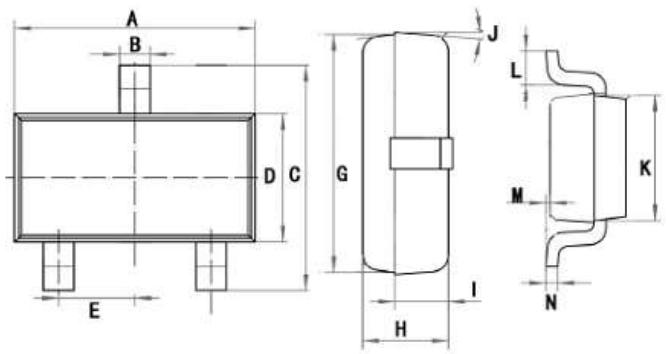
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Mechanical Data



A	2.90±0.1	E	0.950	J	7°	N	$0.15^{+0.03}$
B	0.4±0.01	G	2.85±0.1	K	1.550±0.1		
C	2.80±0.20	H	1.10±0.1	L	0.40		
D	1.60±0.1	I	0.70±0.1	M	0.05±0.03		